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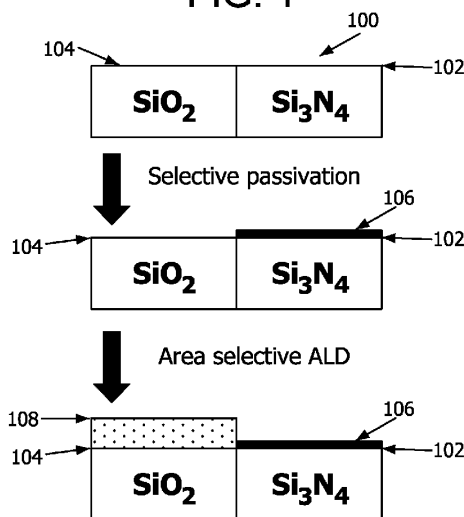
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(54) Title: AREA SELECTIVE DEPOSITION OF DIELECTRIC FILM ON SILICON CONTAINING SURFACES UTILIZING ALCOHOLS

FIG. 1



(57) Abstract: A method for selectively passivating a surface of a substrate, wherein the surface of the substrate includes at least a first surface comprising silicon nitride and at least a second surface comprising a material other than silicon nitride. The method includes the step of exposing the surface to at least one alcohol wherein the alcohol selectively reacts with the silicon nitride to passivate the first surface thereby leaving the second surface substantially unreacted.

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